

Silicon NPN Power Transistors

2SD748 2SD748A

DESCRIPTION

www.datasheet4u.com

- With TO-3 package
- High V_{CBO}
- High power dissipation

APPLICATIONS

- Low frequency power amplifier regulator for TV power supply applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

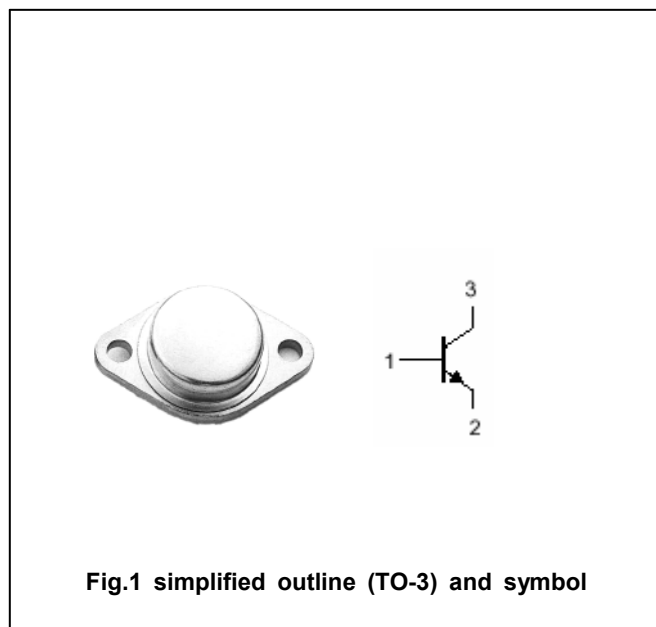


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	250	V
V_{CEO}	Collector-emitter voltage	2SD748	Open base	200	V
		2SD748A		250	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			3	A
I_B	Base current			1	A
P_C	Collector power dissipation		$T_C = 25 \square$	80	W
T_j	Junction temperature			150	$\square$
T_{stg}	Storage temperature			-45~150	$\square$

Silicon NPN Power Transistors

2SD748 2SD748A

CHARACTERISTICS

T_j=25°C unless otherwise specified

www.datasheet4u.com

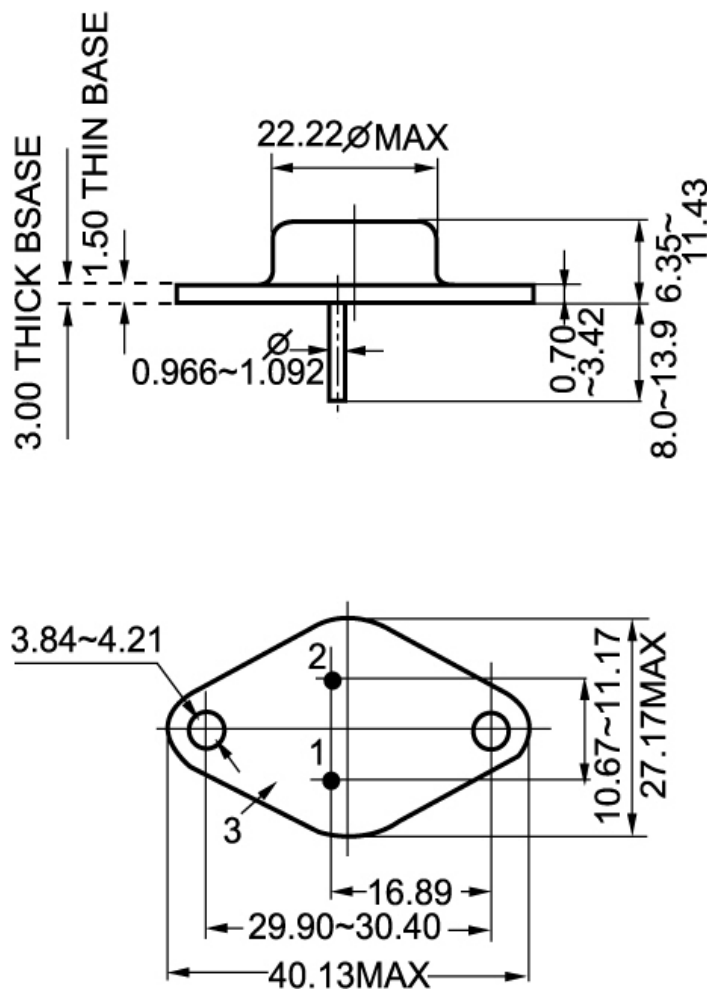
SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SD748	I _C =10mA ; R _{BE} =∞	200			V
		2SD748A		250			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =5mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =3A ; I _B =0.6A			1.0	V
V _{BE}	Base-emitter on voltage		I _C =1A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =200V ; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =5V ; I _C =0			1.0	mA
h _{FE}	DC current gain		I _C =1A ; V _{CE} =5V	25		200	

Silicon NPN Power Transistors

2SD748 2SD748A

PACKAGE OUTLINE

www.datasheet4u.com

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)